N-channel Enhancement Mode Power MOSFET

Features

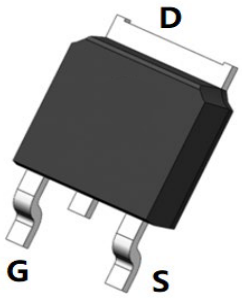
- VDS= 250, ID= 30 A
  RDS(ON) < 800 mΩ @ VGS = 10V
  RDS(ON) < 960 mΩ @ VGS =4.5V

General Features

- Advanced Trench Technology
- Provide Excellent RDS(ON) and Low Gate Charge
- Lead Free and Green Available

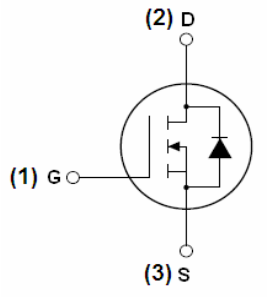
100% UIS TESTED!
100% ΔVds TESTED!

RoHS



TO-252-2L Top View

Pin Assignment



Schematic Diagram

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)					
PARAMETER			**SYMBOL**	**LIMIT**	**UNIT**
Drain-Source Voltage			V_{DS}	250	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current	V_{GS} at 10 V	T_C = 25 °C	I_D	4.5	A
		T_C = 100 °C		3.0	
Pulsed Drain Current[a]			I_{DM}	16	
Linear Derating Factor				0.33	W/°C
Linear Derating Factor (PCB Mount)[e]				0.020	
Single Pulse Avalanche Energy[b]			E_{AS}	130	mJ
Repetitive Avalanche Current[a]			I_{AR}	4.5	A
Repetitive Avalanche Energy[a]			E_{AR}	5.2	mJ
Maximum Power Dissipation	T_C = 25 °C		P_D	45	W
Maximum Power Dissipation (PCB Mount)[e]	T_A = 25 °C			2.5	
Peak Diode Recovery dV/dt[c]			dV/dt	4.8	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)[d]	for 10 s			260	

Notes
a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. V_{DD} = 50 V; starting T_J = 25 °C, L = 14 mH, R_g = 25 Ω, I_{AS} = 3.8 A (see fig. 12).
c. I_{SD} ≤ 3.8 A, dI/dt ≤ 90 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C.
d. 1.6 mm from case.
e. When mounted on 1" square PCB (FR-4 or G-10 material) .

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient (PCB Mount)[a]	R_{thJA}	-	50	°C/W
Maximum Junction-to-Ambient	R_{thJA}	-	110	
Maximum Junction-to-Case	R_{thJC}	-	3.0	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	250	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA	-	0.36	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 250 V, V_{GS} = 0 V	-	-	25	µA
		V_{DS} = 200 V, V_{GS} = 0 V, T_J = 125 °C	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 2.3 A[b]	-		0.8	Ω
Forward Transconductance	g_{fs}	V_{DS} = 50 V, I_D = 2.3 A[b]	1.5	-	-	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz, see fig. 5[c]	-	260	-	pF
Output Capacitance	C_{oss}		-	77	-	
Reverse Transfer Capacitance	C_{rss}		-	15	-	
Total Gate Charge	Q_g	V_{GS} = 10 V, I_D = 4.4 A, V_{DS} = 200 V, see fig. 6 and 13[b, c]	-	-	14	nC
Gate-Source Charge	Q_{gs}		-	-	2.7	
Gate-Drain Charge	Q_{gd}		-	-	7.8	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 125 V, I_D = 4.4 A, R_G = 18 Ω, R_D = 28 Ω, see fig. 10[b, c]	-	7.0	-	ns
Rise Time	t_r		-	13	-	
Turn-Off Delay Time	$t_{d(off)}$		-	20	-	
Fall Time	t_f		-	12	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	3.8	A
Pulsed Diode Forward Current[a]	I_{SM}		-	-	15	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = 3.8 A, V_{GS} = 0 V[b]	-	-	1.8	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = 4.4 A, dI/dt = 100 A/µs[b]	-	200	400	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	0.93	1.9	µC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

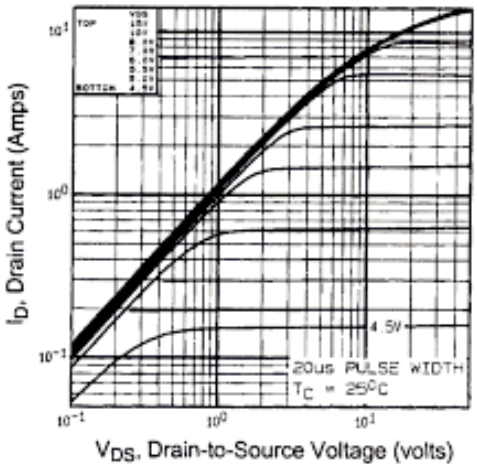


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

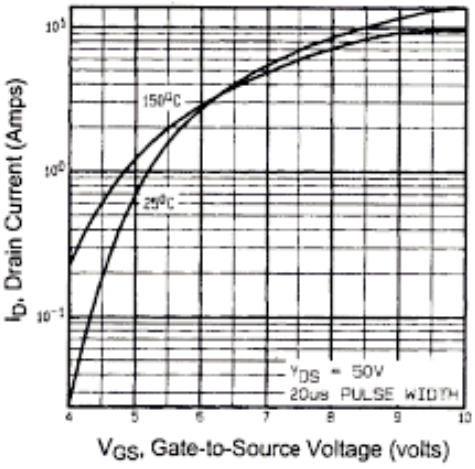


Fig. 3 - Typical Transfer Characteristics

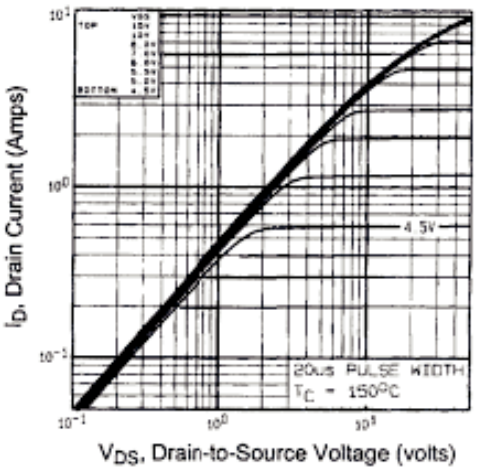


Fig. 2 - Typical Output Characteristics, T_C = 150 °C

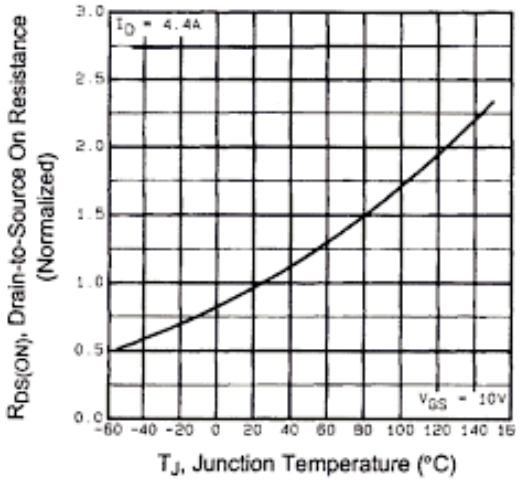


Fig. 4 - Normalized On-Resistance vs. Temperature

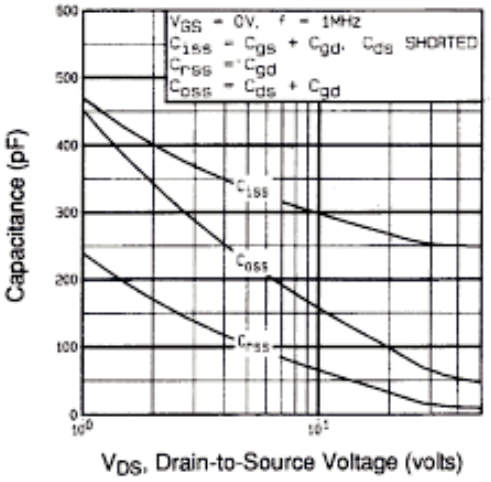


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

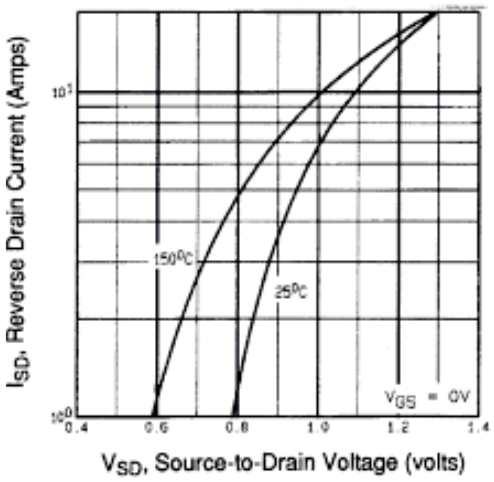


Fig. 7 - Typical Source-Drain Diode Forward Voltage

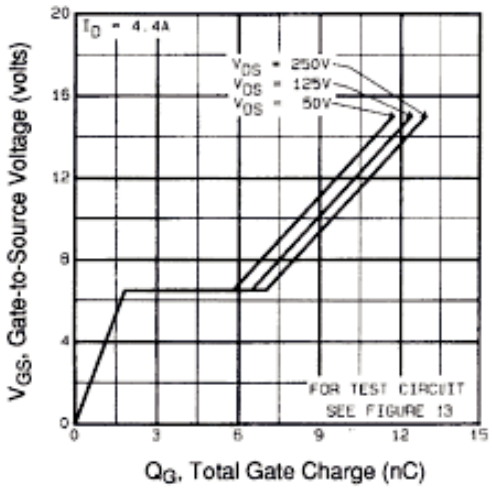


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

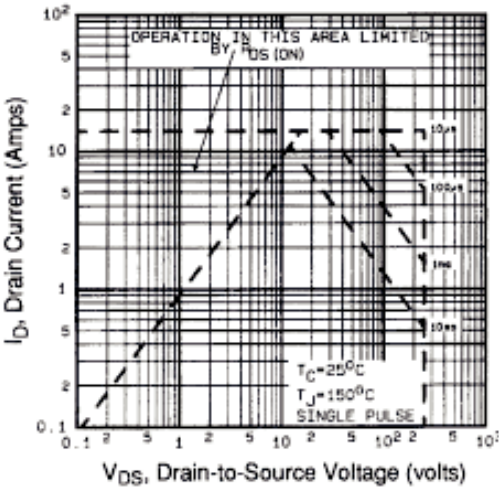


Fig. 8 - Maximum Safe Operating Area

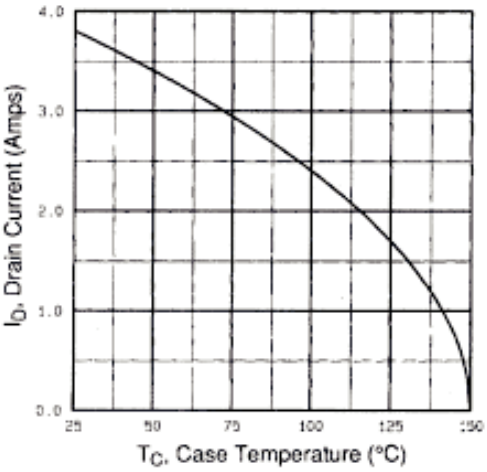


Fig. 9 - Maximum Drain Current vs. Case Temperature

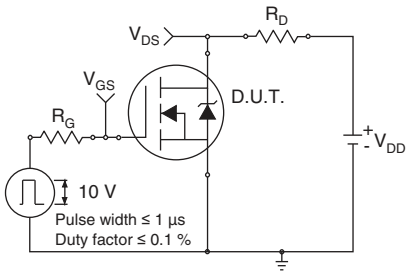


Fig. 10a - Switching Time Test Circuit

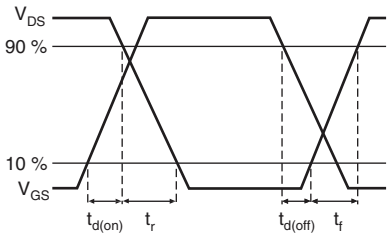


Fig. 10b - Switching Time Waveforms

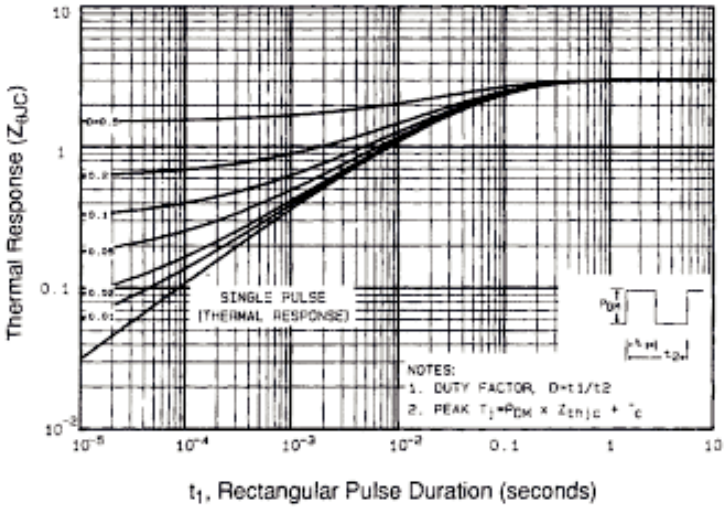


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

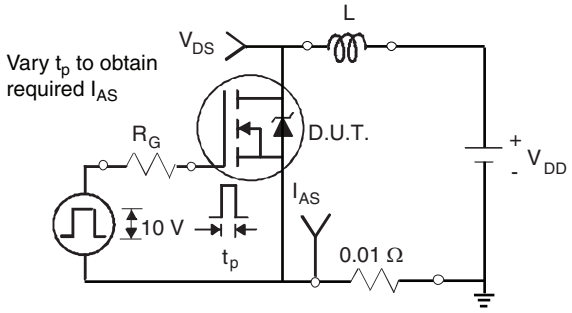


Fig. 12a - Unclamped Inductive Test Circuit

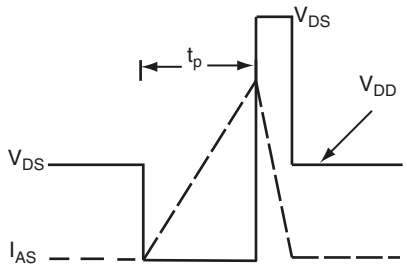


Fig. 12b - Unclamped Inductive Waveforms

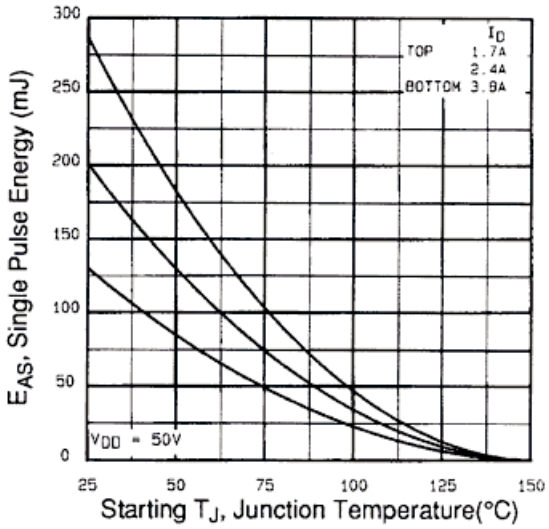


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

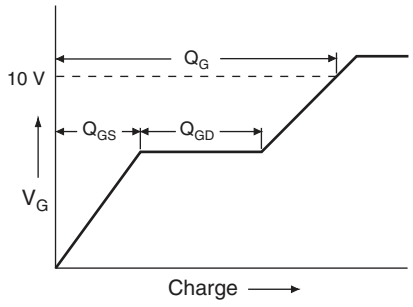


Fig. 13a - Basic Gate Charge Waveform

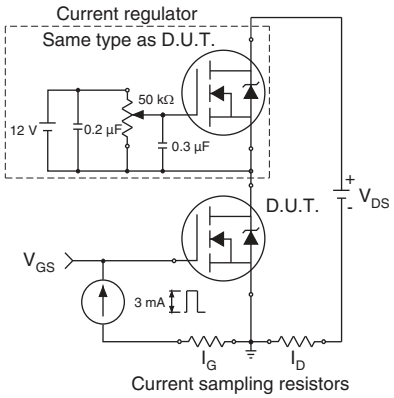
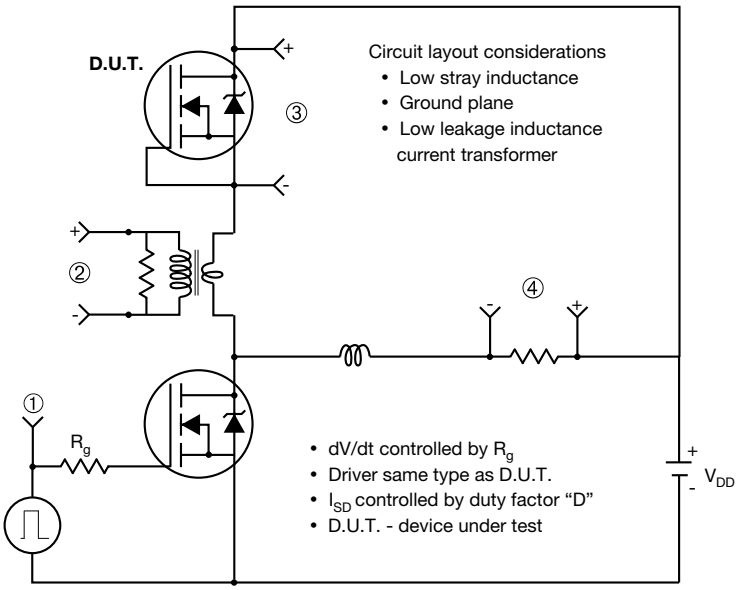
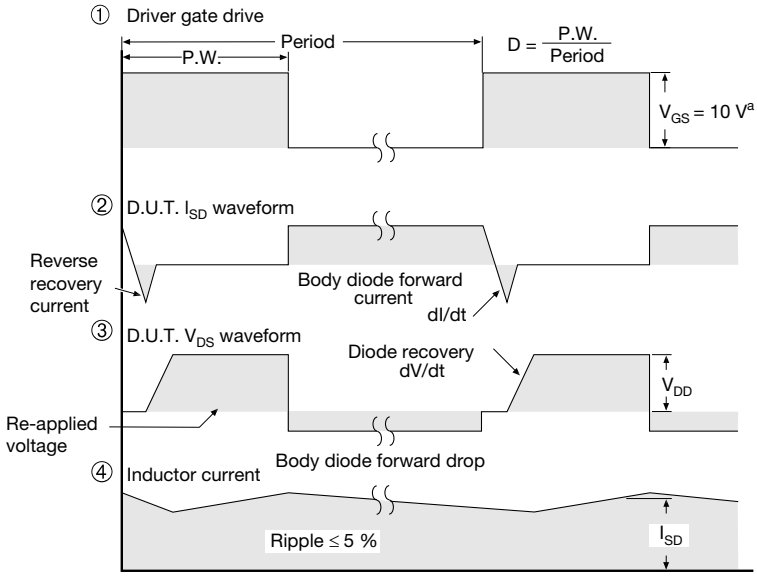


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit





Note

a. V_{GS} = 5 V for logic level devices

Fig. 14 - For N-Channel